

application 09/114,847, now issued as U.S. Patent No. 6,201,276 B1. Also included are mixtures of any of the gases or types of gases described above. Exemplary non-plasma process parameters using these other gases include a flow rate of about 2 sccm to about 400 sccm for these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please amend claim 73 as follows:

C10
C2
Twice Amended 73. (Twice Amended) An in-process device, comprising:
a substrate; and
a conductive layer over the substrate, the conductive layer being exposed to a material selected from the group consisting of diborane, phosphine, and a carbon-silicon compound to reduce an ability of the conductive layer to associate with oxygen.

Please add new claim 76 as follows:

C3
--76. (New) The in-process device of claim 73 wherein the carbon-silicon compound is selected from the group consisting of methylsilane, hexamethyldisilane, and hexamethyldisilazane.--

REMARKS

Claims 73-75 along with newly added claim 76 are currently pending in the present patent-application. In a final Office Action mailed 15 July 2002, the Examiner rejected claims 73-75 under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,303,510 B1 to Chien *et al.* ("Chien").

Applicant's invention exposes a conductive layer to an oxygen-inhibiting material prior to the formation of the another layer or layers on the conductive layer to substantially